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# **MMDT440**

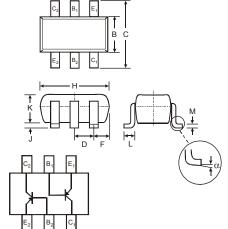
## **DUAL PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR**

# **Features**

- **Epitaxial Planar Die Construction**
- Ideal for Low Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 3)
- "Green" Device (Note 4 and 5)

## **Mechanical Data**

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: K2T See Page 4
- Ordering & Date Code Information: See Page 4
- Weight: 0.006 grams (approximate)



	SOT-363									
Dim	Min	Max								
Α	0.10	0.30								
В	1.15	1.35								
С	2.00	2.20								
D	0.65 Nominal									
F	0.30	0.40								
Н	1.80	2.20								
J	_	0.10								
K	0.90	1.00								
L	0.25	0.40								
М	0.10	0.25								
α	0°	8°								
All Din	All Dimensions in mm									

# **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Collector-Base Voltage		$V_{CBO}$	-40	V
Collector-Emitter Voltage		V <sub>CEO</sub>	-40	V
Emitter-Base Voltage		$V_{EBO}$	-5.0	V
Collector Current - Continuous	(Note 1)	I <sub>C</sub>	-600	mA
Power Dissipation	(Note 1, 2)	Pd	200	mW
Thermal Resistance, Junction to Ambient	(Note 1)	$R_{ heta JA}$	625	°C/W
Operating and Storage Temperature Range		T <sub>i</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Maximum combined dissipation.
- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

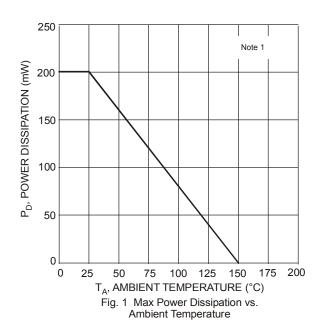
  Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

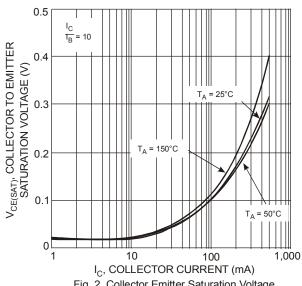


#### **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

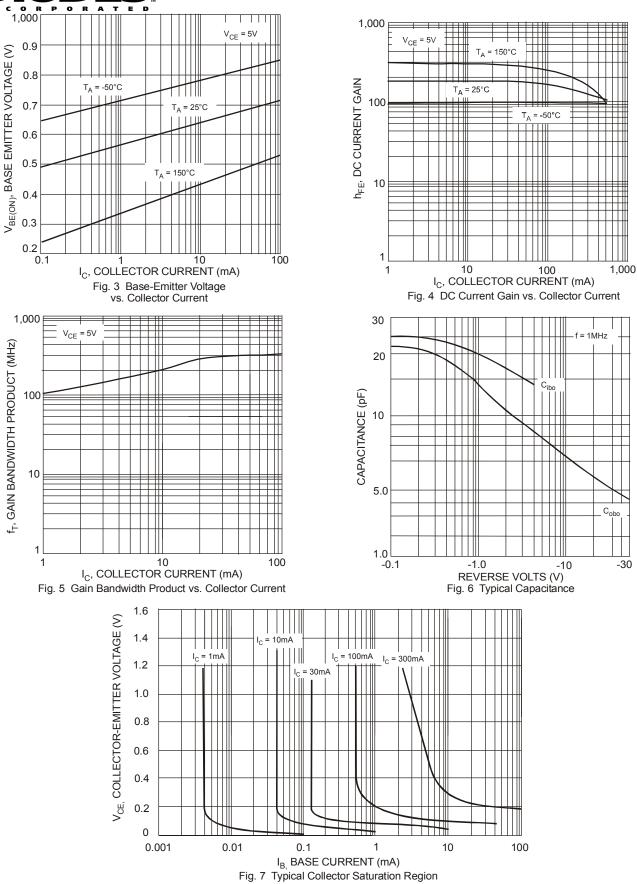
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-40	_	V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40	_	V	$I_C = -1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5.0		V	$I_E = -100 \mu A, I_C = 0$
Collector Cutoff Current	I <sub>CEX</sub>		-100	nA	$V_{CE} = -35V, V_{EB(OFF)} = -0.4V$
Base Cutoff Current	I <sub>BL</sub>		-100	nA	$V_{CE} = -35V, V_{EB(OFF)} = -0.4V$
ON CHARACTERISTICS (Note 6)					
DC Current Gain	h <sub>FE</sub>	30 60 100 100 20	  300 	-	$I_{C} = -100 \mu A, V_{CE} = -1.0 V$ $I_{C} = -1.0 m A, V_{CE} = -1.0 V$ $I_{C} = -10 m A, V_{CE} = -1.0 V$ $I_{C} = -150 m A, V_{CE} = -2.0 V$ $I_{C} = -500 m A, V_{CE} = -2.0 V$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	-0.40 -0.75	<b>V</b>	$I_C$ = -150mA, $I_B$ = -15mA $I_C$ = -500mA, $I_B$ = -50mA
Base-Emitter Saturation Voltage		-0.75 —	-0.95 -1.30	٧	$I_C$ = -150mA, $I_B$ = -15mA $I_C$ = -500mA, $I_B$ = -50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	$C_{cb}$	_	8.5	pF	$V_{CB} = -10V$ , $f = 1.0MHz$ , $I_E = 0$
Input Capacitance	C <sub>eb</sub>	_	30	pF	$V_{EB} = -0.5V$ , $f = 1.0MHz$ , $I_{C} = 0$
Input Impedance	h <sub>ie</sub>	1.5	15	kΩ	
Voltage Feedback Ratio	h <sub>re</sub>	0.1	8.0	x 10 <sup>-4</sup>	V <sub>CE</sub> = -10V, I <sub>C</sub> = -1.0mA,
Small Signal Current Gain	h <sub>fe</sub>	60	500		f = 1.0kHz
Output Admittance	h <sub>oe</sub>	1.0	100	μS	
Current Gain-Bandwidth Product	f <sub>T</sub>	200		MHz	$V_{CE} = -10V, I_{C} = -20mA,$ f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t <sub>d</sub>	_	15	ns	$V_{CC} = -30V, I_{C} = -150mA,$
Rise Time	t <sub>r</sub>	_	20	ns	$V_{BE(off)} = -2.0V, I_{B1} = -15mA$
Storage Time	ts	_	225	ns	$V_{CC} = -30V, I_{C} = -150mA,$
Fall Time	t <sub>f</sub>	_	30	ns	$I_{B1} = I_{B2} = -15\text{mA}$

Notes: 6. Short duration pulse test used to minimize self-heating effect.









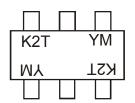


#### Ordering Information (Note 7)

Device	Packaging	Shipping		
MMDT4403-7-F	SOT-363	3000/Tape & Reel		

7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**



K2T = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002 M = Month ex: 9 = September

Date Code Key

ĺ	Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
ĺ	Code	J	K	L	М	N	Р	R	S	Т	U	V	W	Х	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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